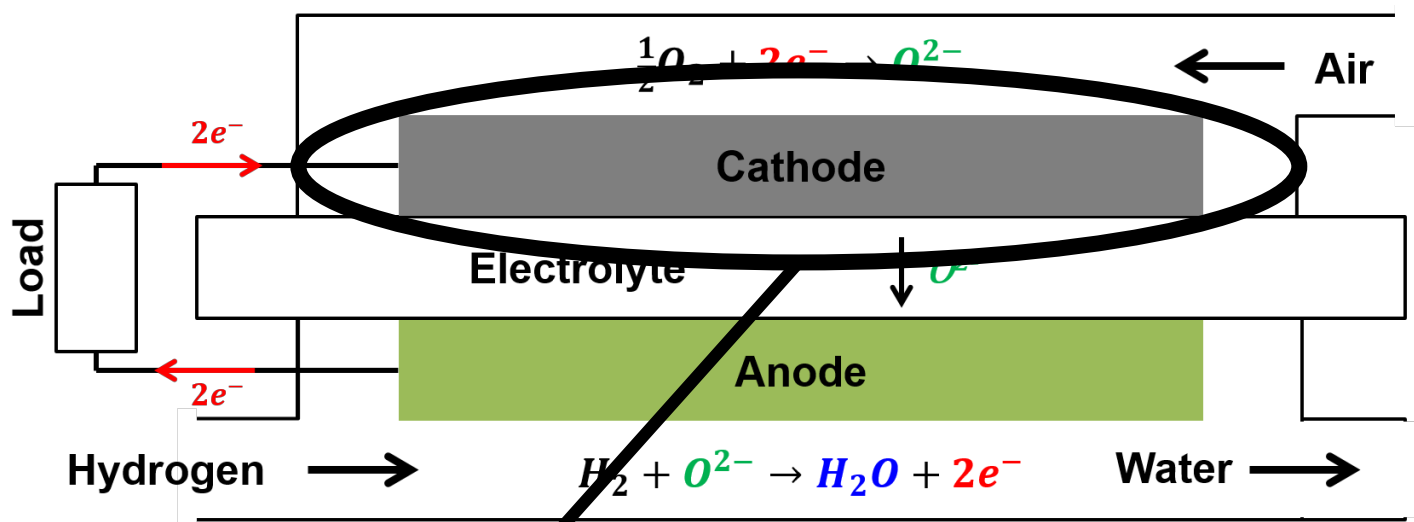


Self-Regulation of Surface Chemistry in Oxygen Electrodes for Solid Oxide Fuel Cells

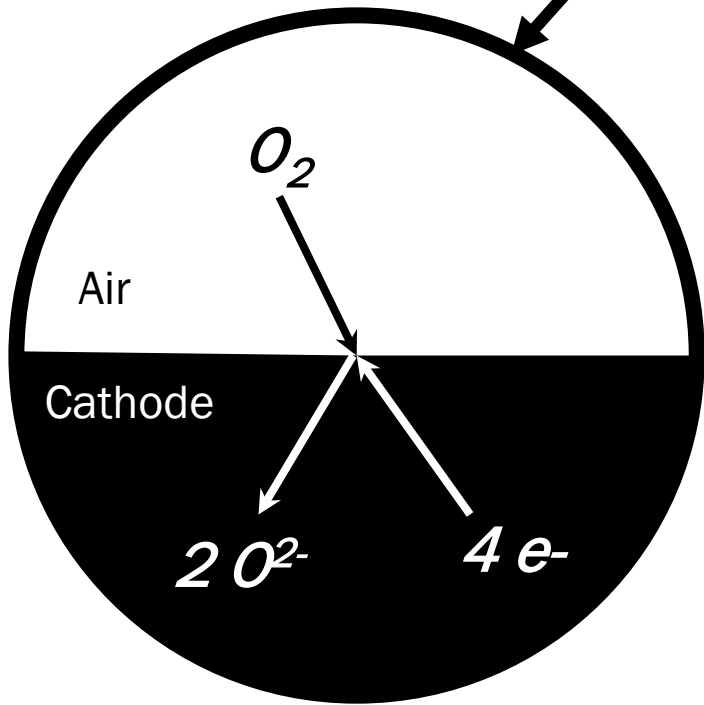
[Clement Nicollet](#), Harry Tuller
Massachusetts Institute of Technology
NETL Award DE-FE0026109 Phase 1
Program Manager: Dr. Joseph Stoffa

Solid Oxide Fuel Cells



High efficiency
Fuel flexibility
Highly scalable
Produces usable steam (CHP applications)

Main drawback to address:
performance degradation

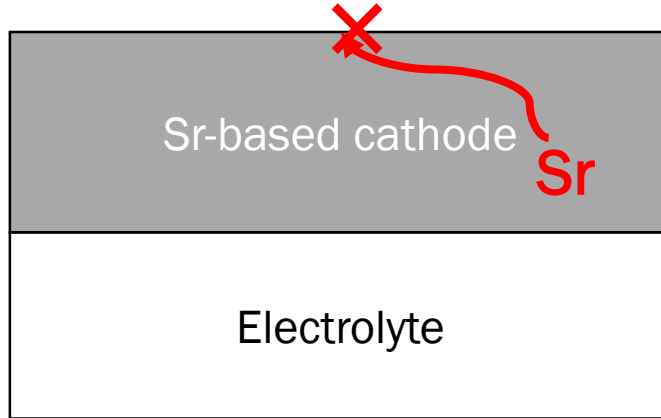


Oxygen Reduction Reaction limited by solid/gas surface exchange reaction rate

Surface reaction very sensitive to contaminants
→ major source of performance degradation

Main sources of cathode performance degradation

Sr segregation

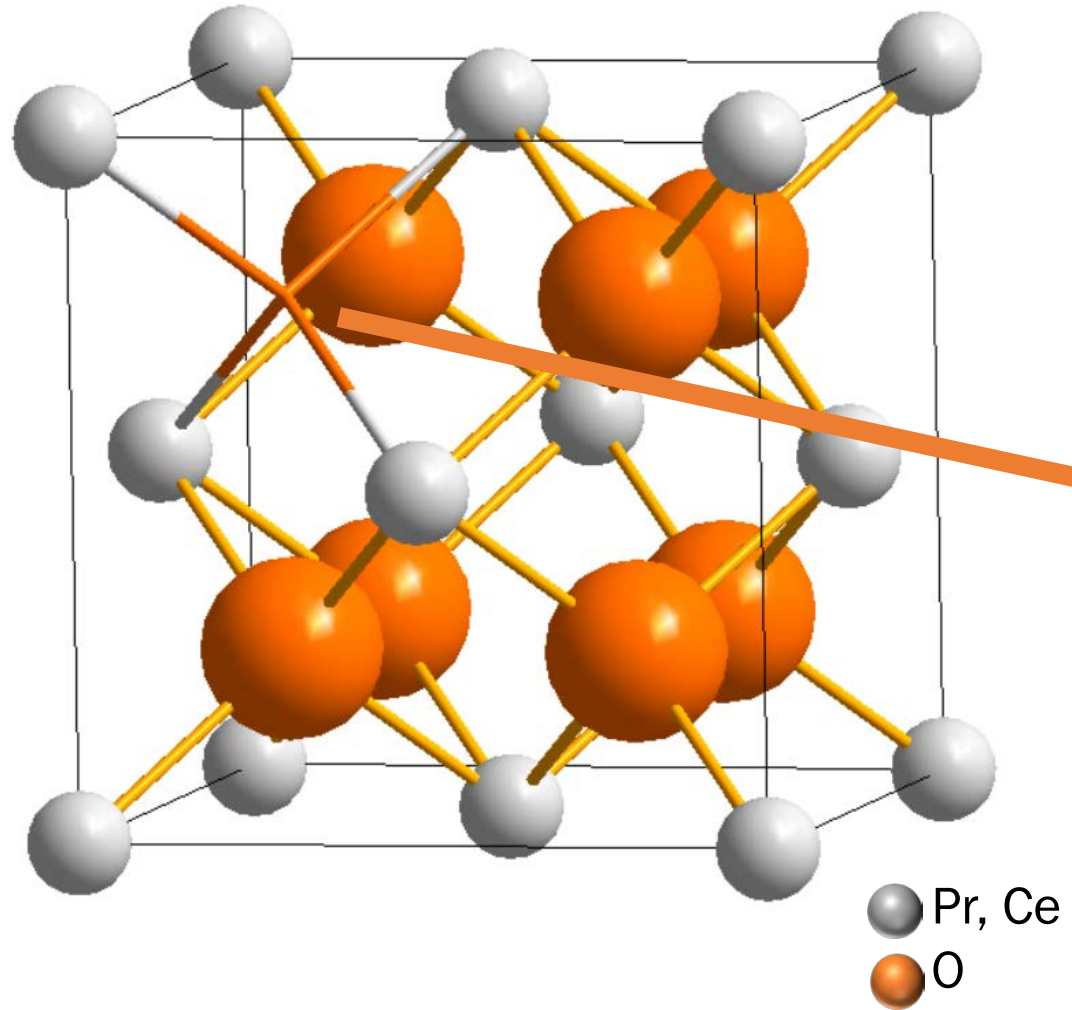


How to avoid Sr segregation?

Formation of surface SrO
blocking active sites

*W. Jung, H.L. Tuller,
Energy Environ. Sci., 2012, 5, 5370–5378*

Sr-free cathode material – Pr doped ceria (PCO)



Fluorite CaF_2 type structure

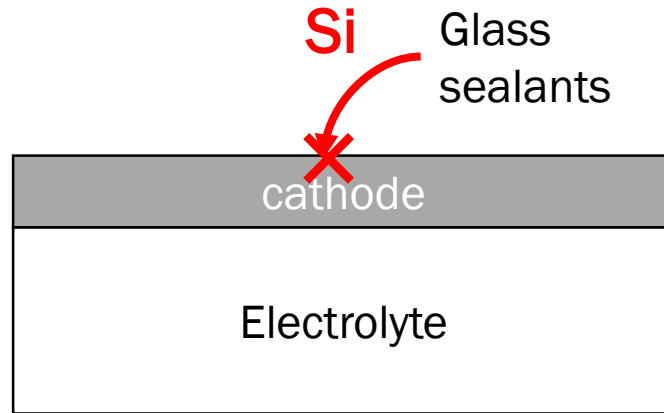
Pr mixed valence $3+/4+$



O^{2-} vacancies

High O^{2-} Diffusion &
Electrochemical activity
Sr-free

Si poisoning



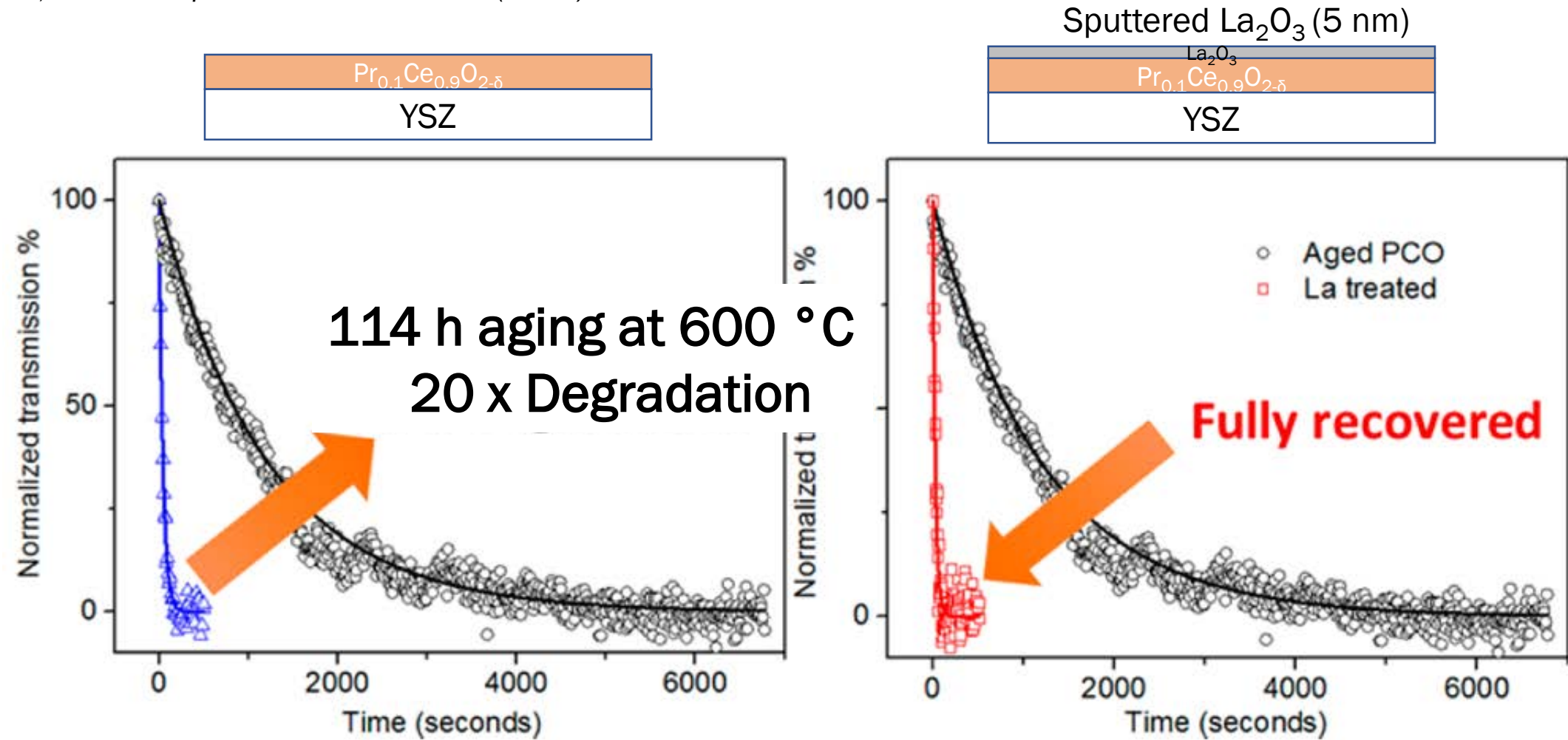
Formation of insulating silica
blocking active sites

Silicon poisoning observed on YSZ/Pt
system (*Hertz, Rothschild, Tuller, J.
Electroceram. 22 (2009) 428-435*)

How to limit Si poisoning of
Pr-doped ceria electrodes?

Scavenging Si poison with La_2O_3 in Pr-doped ceria films

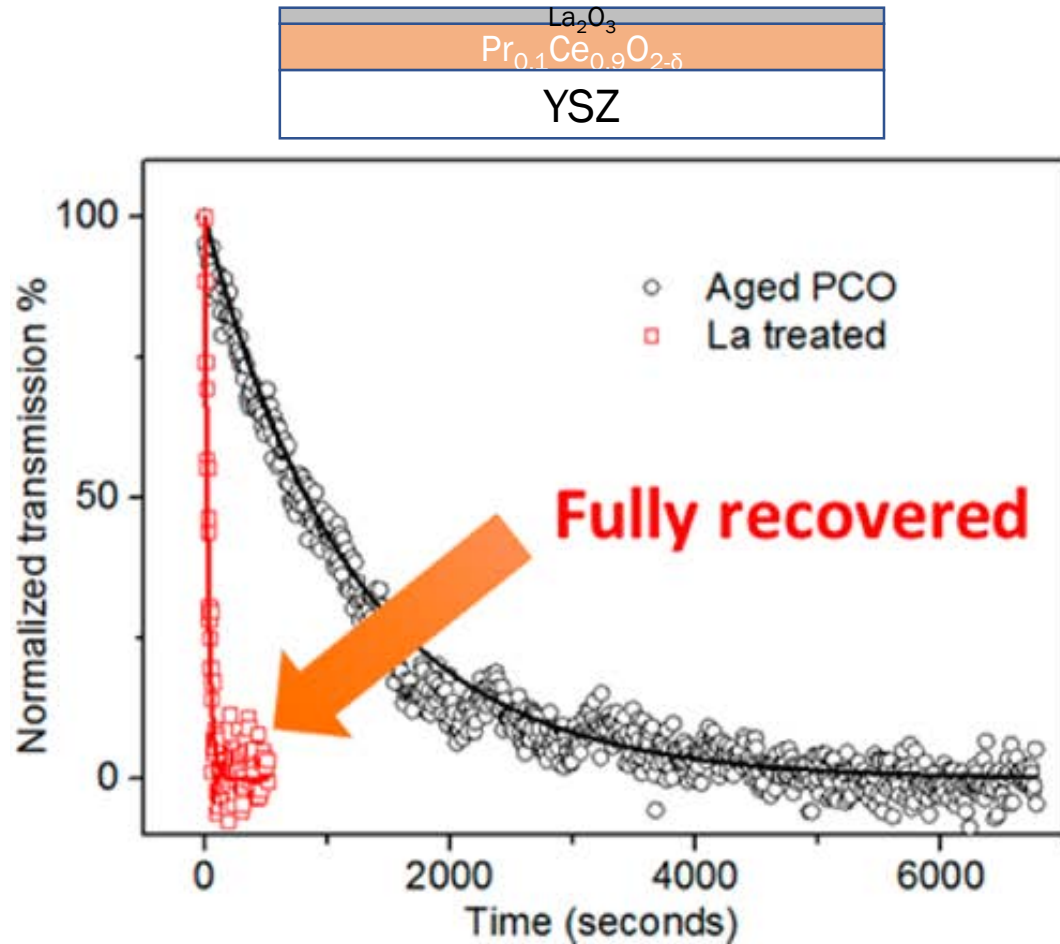
L. Zhao, S.R. Bishop et al. Chem. Mat. 27 (2015) 3065-3070



La layer traps Si → surface exchange rate recovered

Scavenging Si poison with La_2O_3 in Pr-doped ceria films

L. Zhao, S.R. Bishop et al. *Chem. Mat.* 27 (2015) 3065-3070

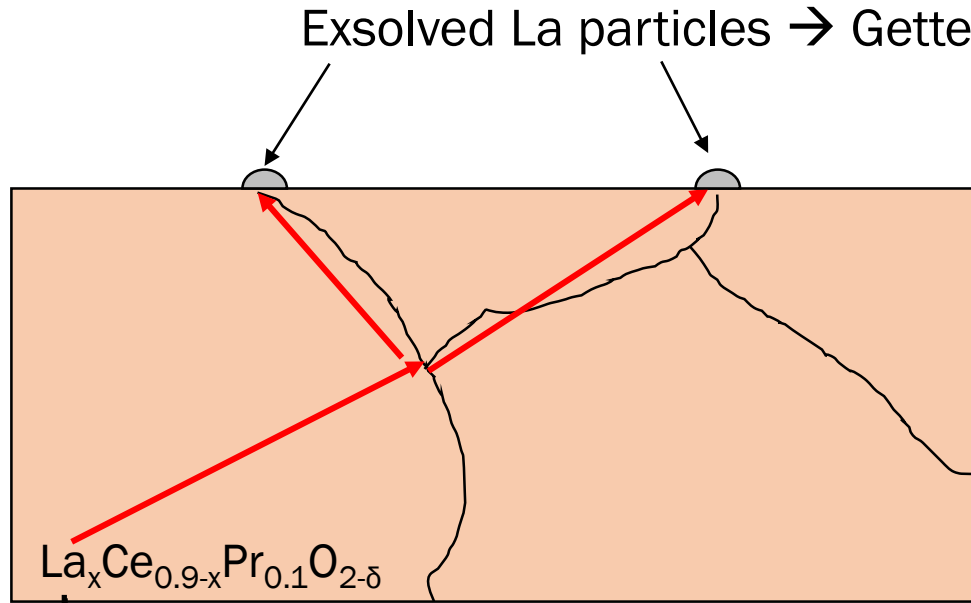


La_2O_3 sputtering \rightarrow not practical under operation
How to continuously getter Si poisoning?

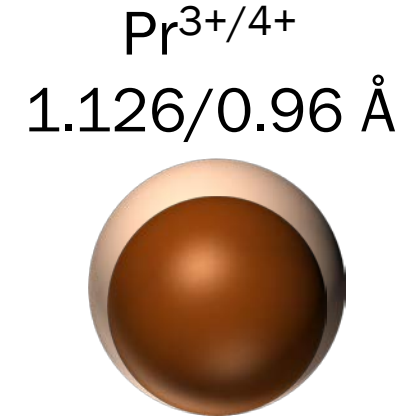
Lanthanum bulk doping for Si trapping

Self-regulation of surface poisoning with La doping

Internal renewable source of La getter



Scavenging element introduced into ceria in high concentration

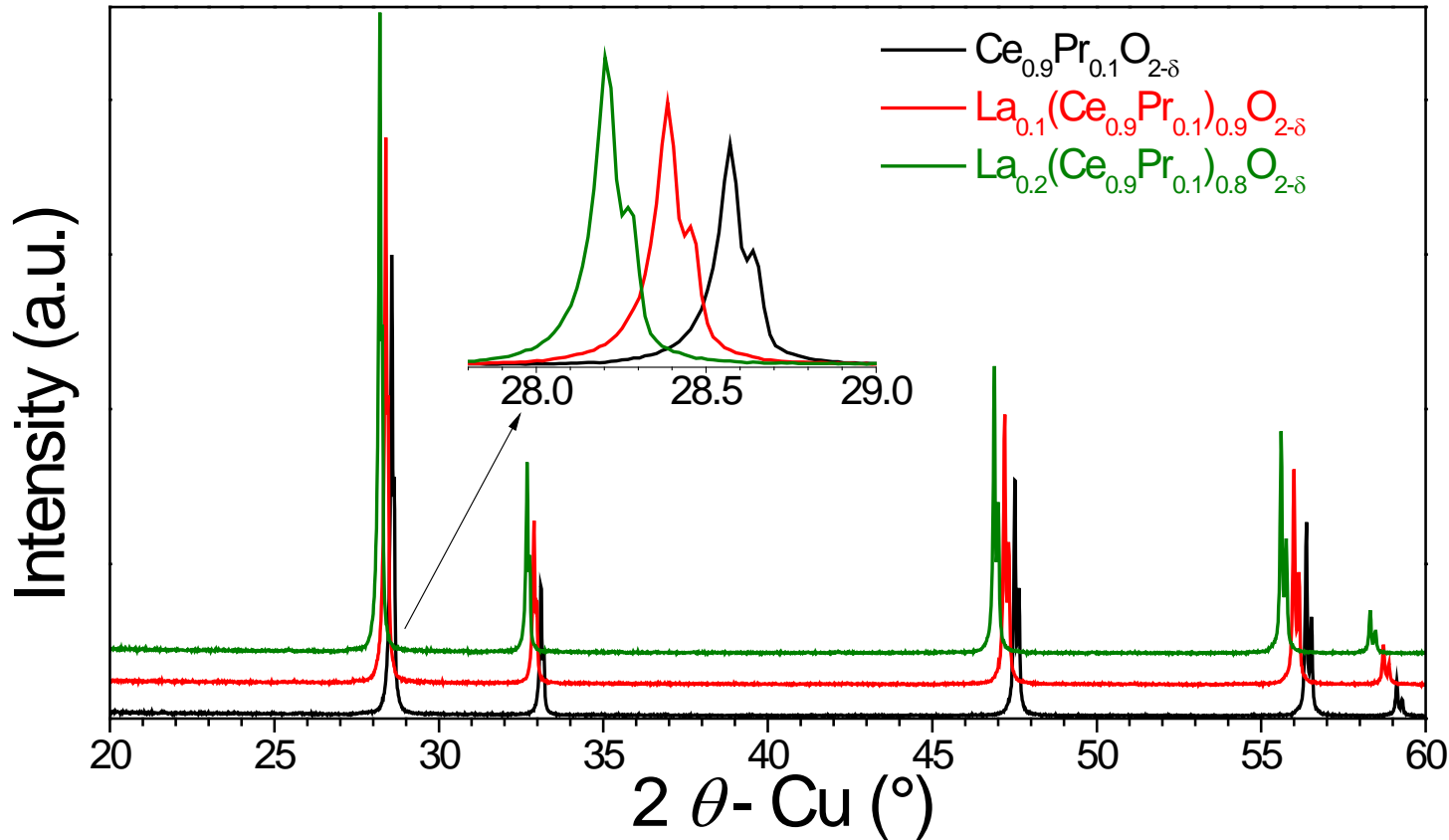


Source of scavenging elements to enable long term operation

Self-Cleaning Material

X-ray diffraction on synthesized powders

Fluorite structure (SG: Fm-3m)

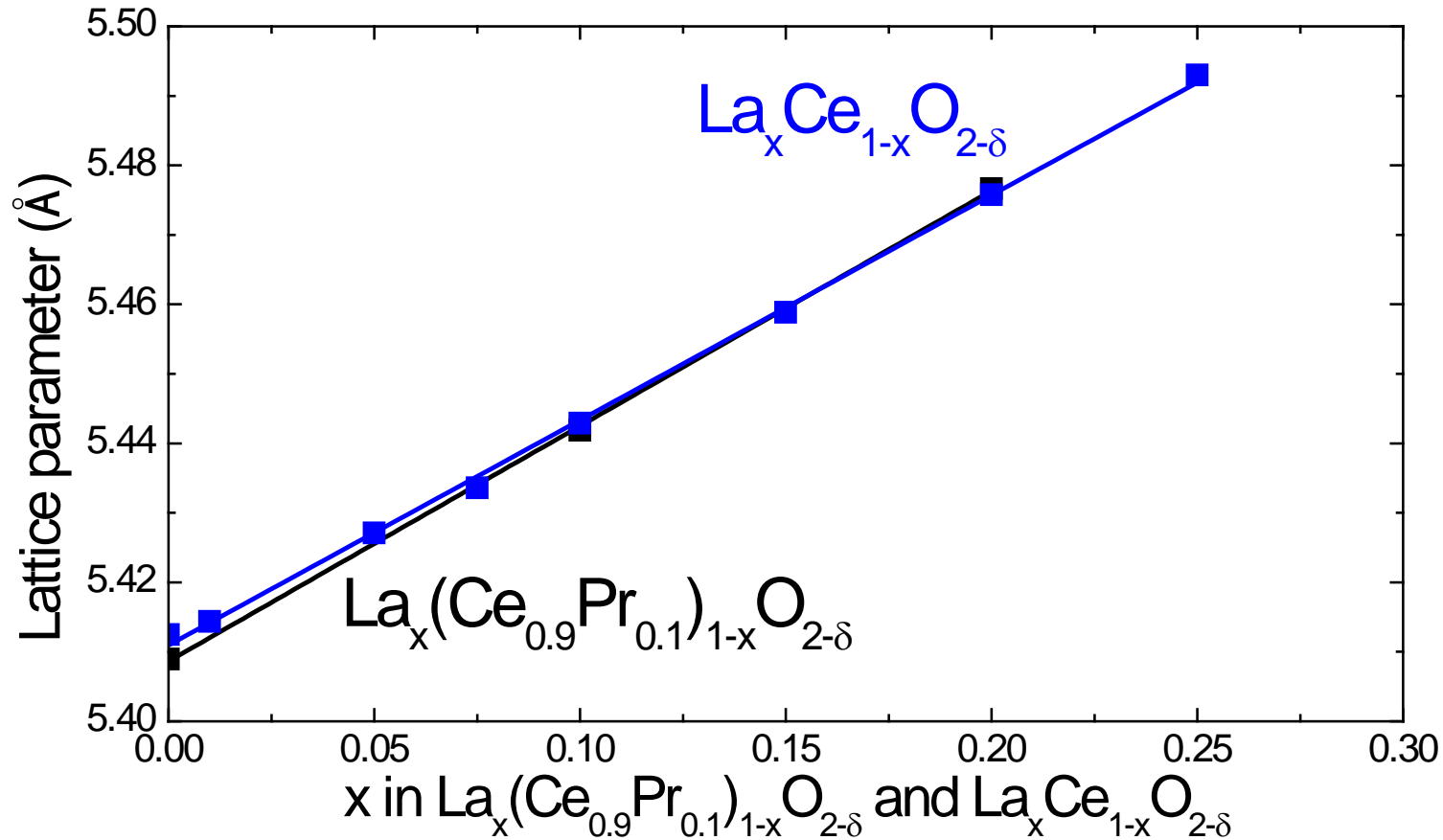


La insertion in ceria
Significant increase in lattice parameter

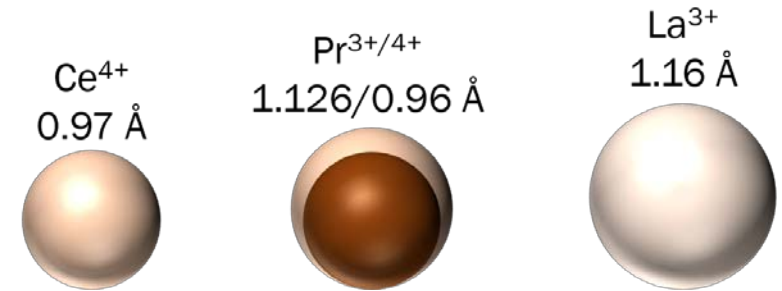
No impurities \rightarrow La fully soluble in PCO

X-ray Diffraction - Lattice parameters

Comparison of lattice parameters with $\text{La}_x\text{Ce}_{1-x}\text{O}_{2-\delta}$ solid solution

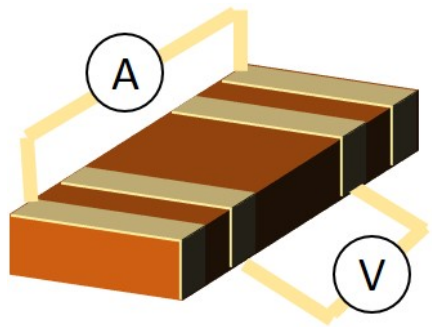


No difference in lattice parameter

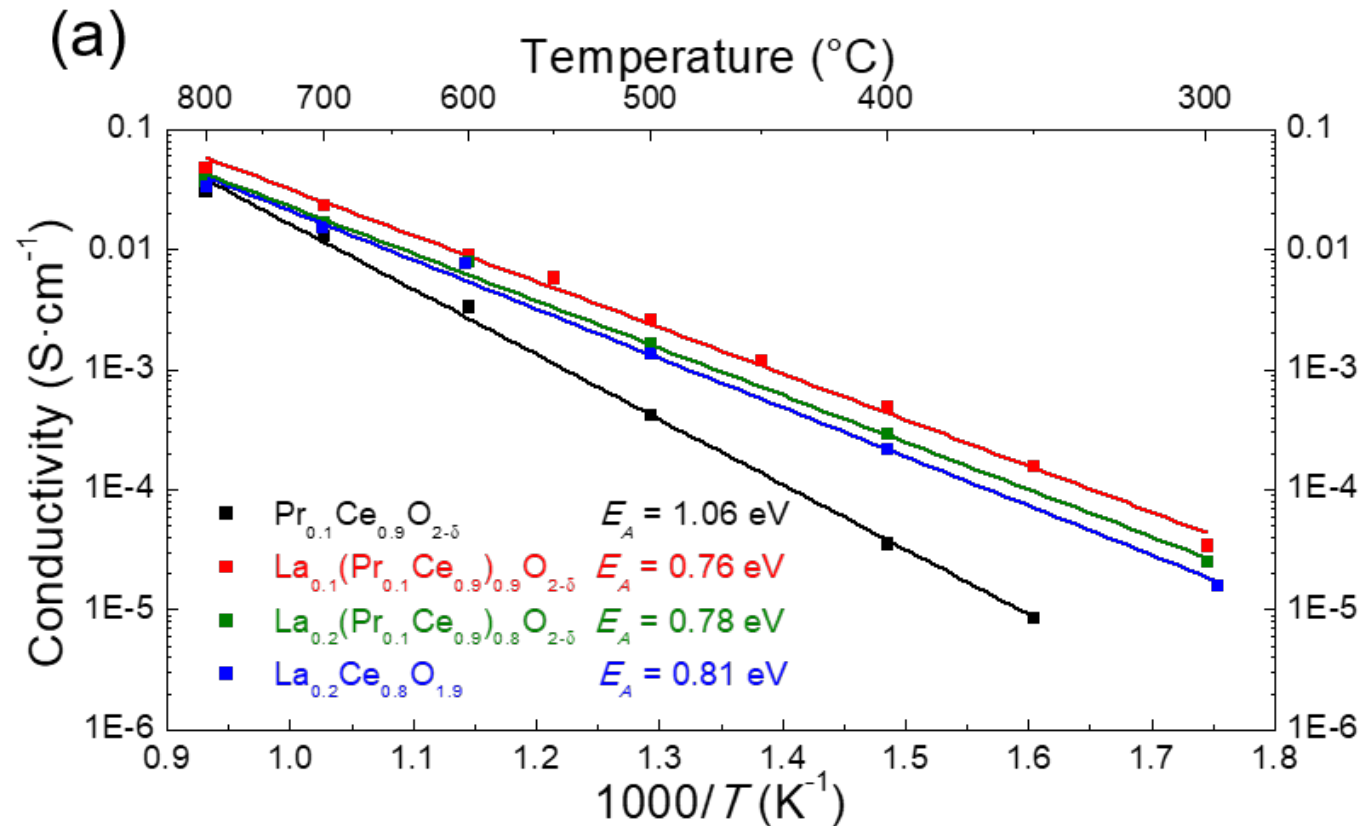


La insertion forces Pr in 4+ state?
Influence on transport properties?

Transport properties: Electrical Conductivity



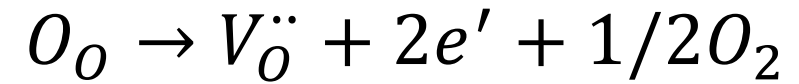
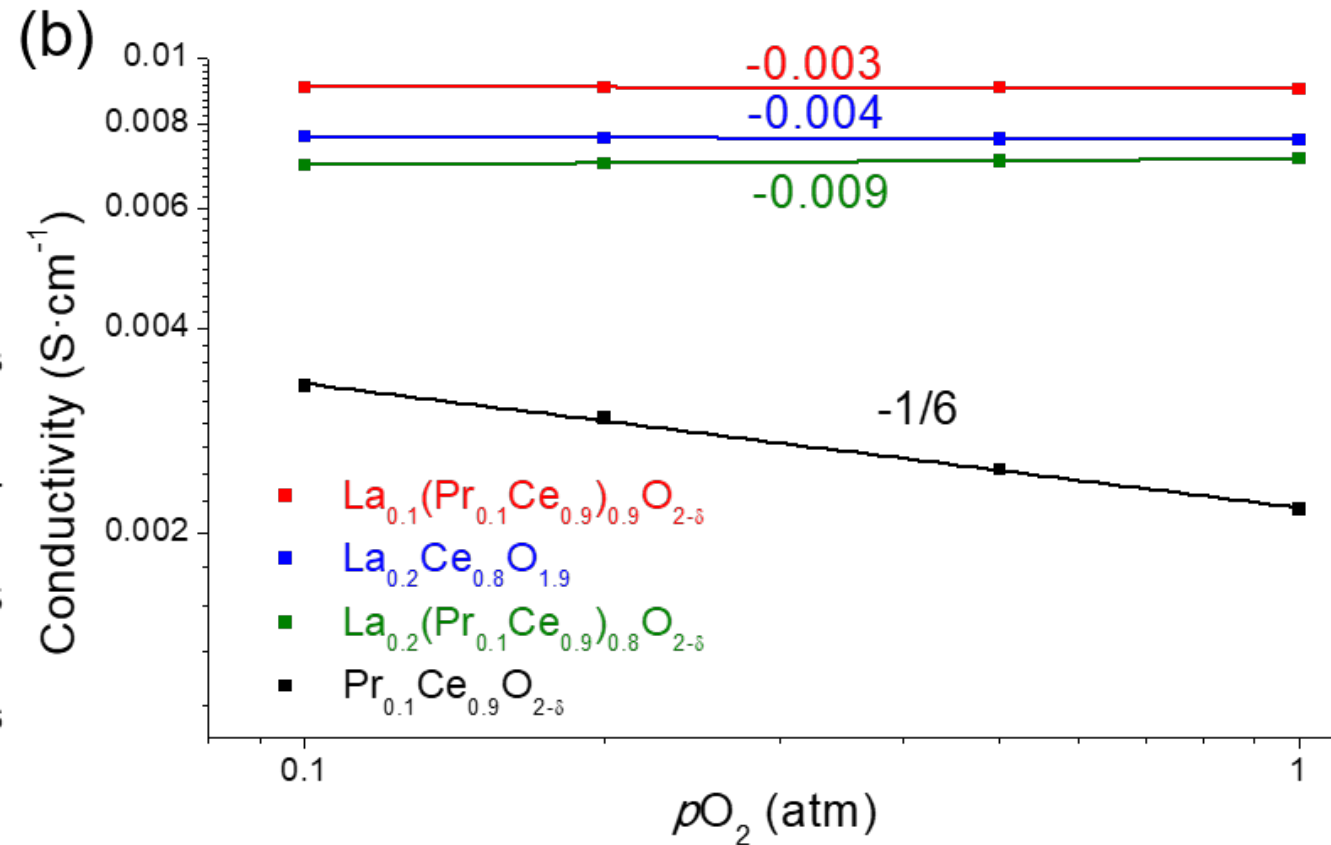
Four points conductivity measurements



La doping increases
vacancy concentration

Lower E_a : vacancy concentration
less dependant on
Pr oxidation state

pO_2 dependance of conductivity



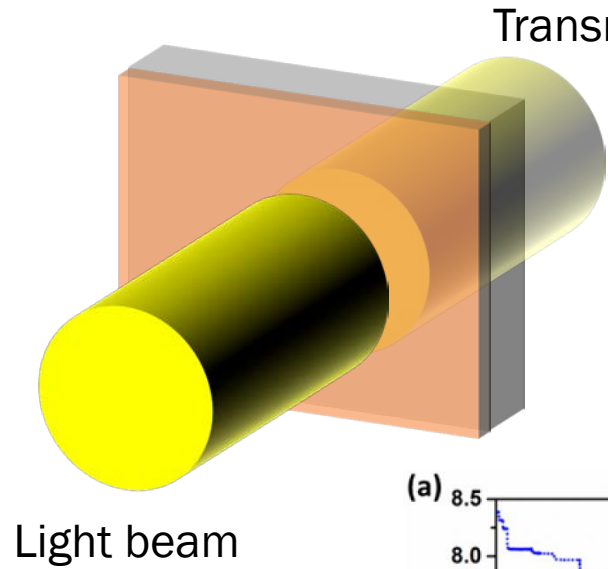
$$[V_{\ddot{O}}] \cdot n^2 p_{O_2}^{1/2} = K_r$$

La-doping: ionic conductivity ↗
 e- conductivity ↘
 Influence on Surface Exchange Rate?

Influence of La doping on surface exchange rates

Optical Absorption in $\text{Ce}_{0.9}\text{Pr}_{0.1}\text{O}_{2-\delta}$

Pr doped ceria film (PLD) on Y-doped zirconia substrate*



Color of PCO depends on Pr valence

Absorption \leftrightarrow oxygen non-stoichiometry

Beer-Lambert law

$$\alpha_{Pr^{4+}} = \epsilon_{Pr^{4+}} [Pr^{4+}]$$

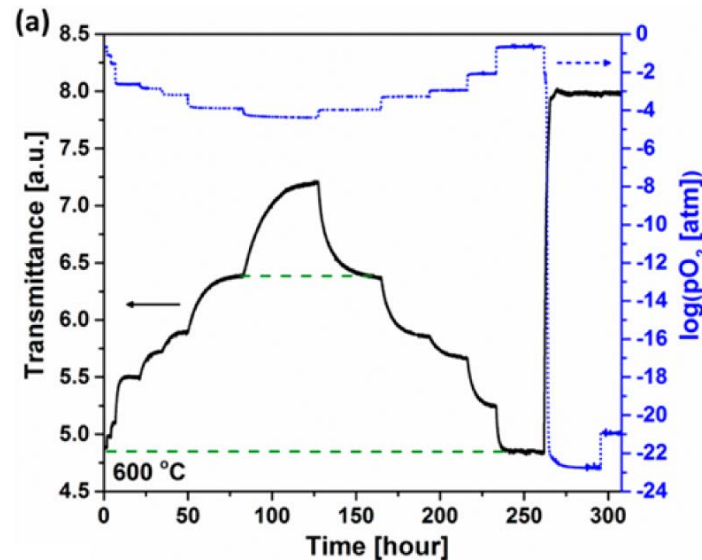
Step in pO_2



Transmittance Relaxation

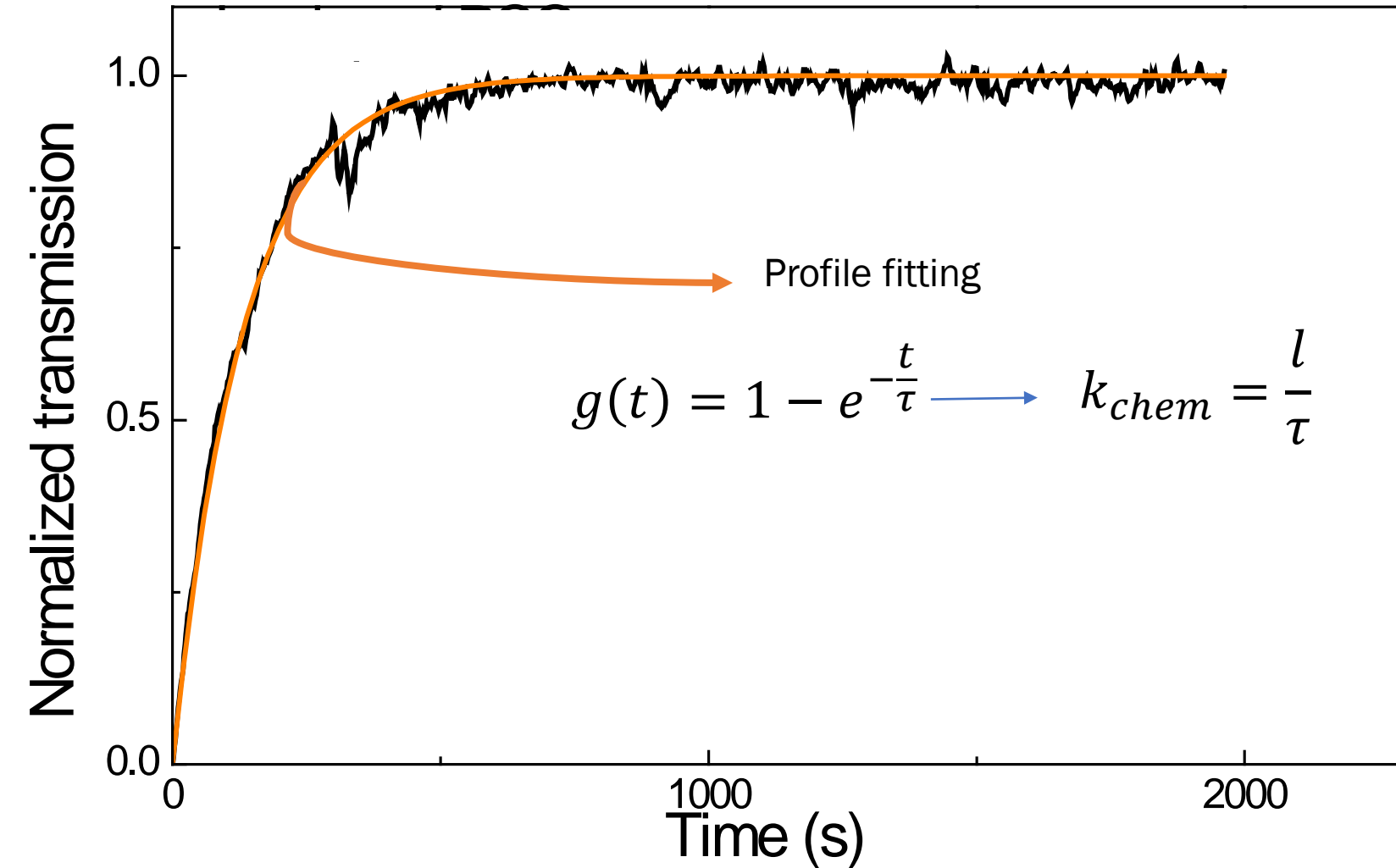


Surface exchange coefficient



*single crystal substrate

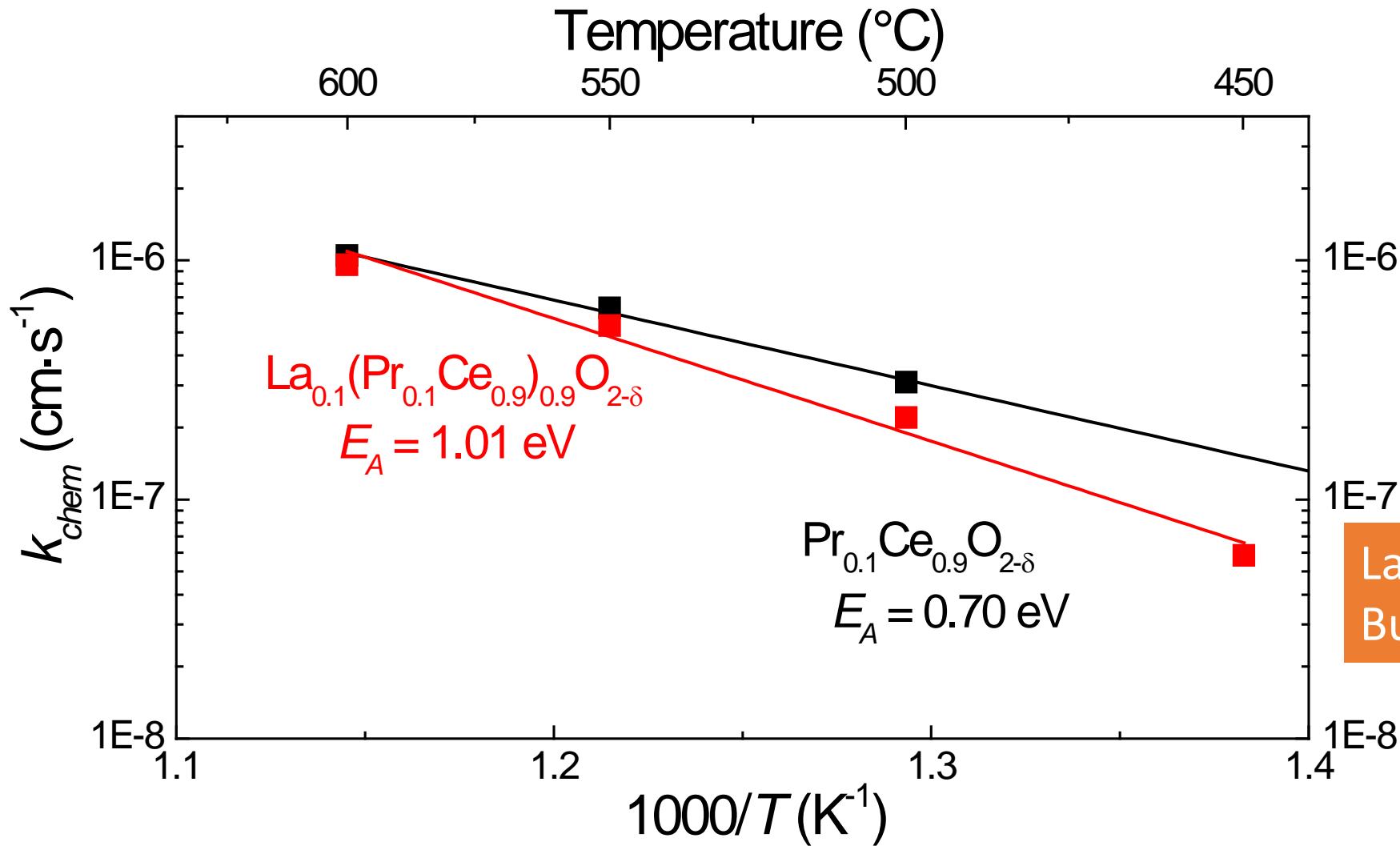
Optical transmission relaxation (pO_2 step 0.1-0.2 atm)



Effect of La doping on surface exchange rate?

Influence of La doping On surface exchange coefficient

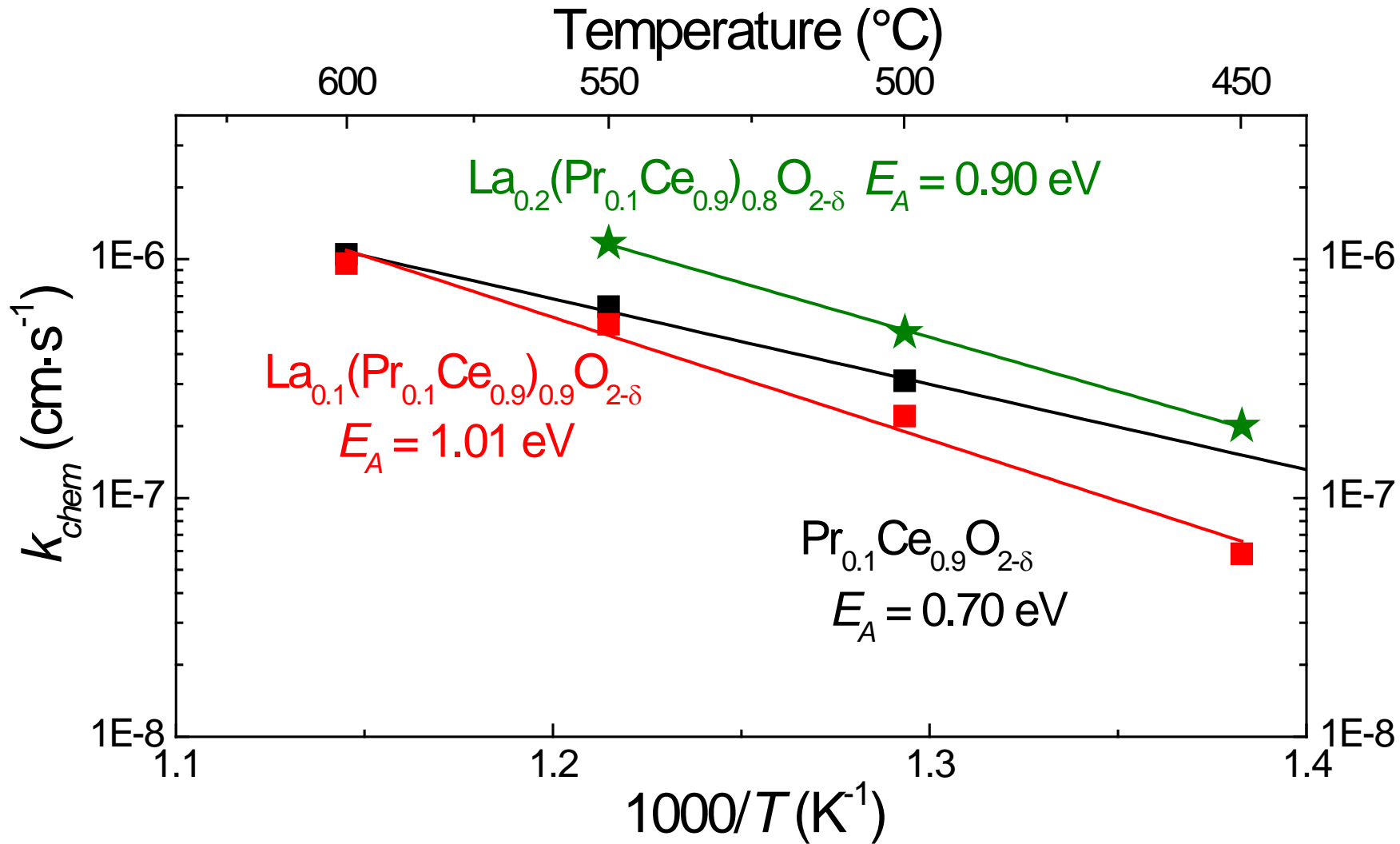
Optical Absorption in $\text{La}_x(\text{Ce}_{0.9}\text{Pr}_{0.1})_{1-x}\text{O}_{2-\delta}$



La doping \rightarrow ionic conductor
But weak influence on k_{chem}

Influence of La doping On surface exchange coefficient

Optical Absorption in $\text{La}_x(\text{Ce}_{0.9}\text{Pr}_{0.1})_{1-x}\text{O}_{2-\delta}$

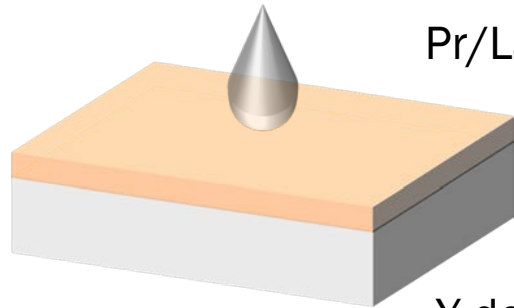


La segregation?

Resistance to Silicon poisoning

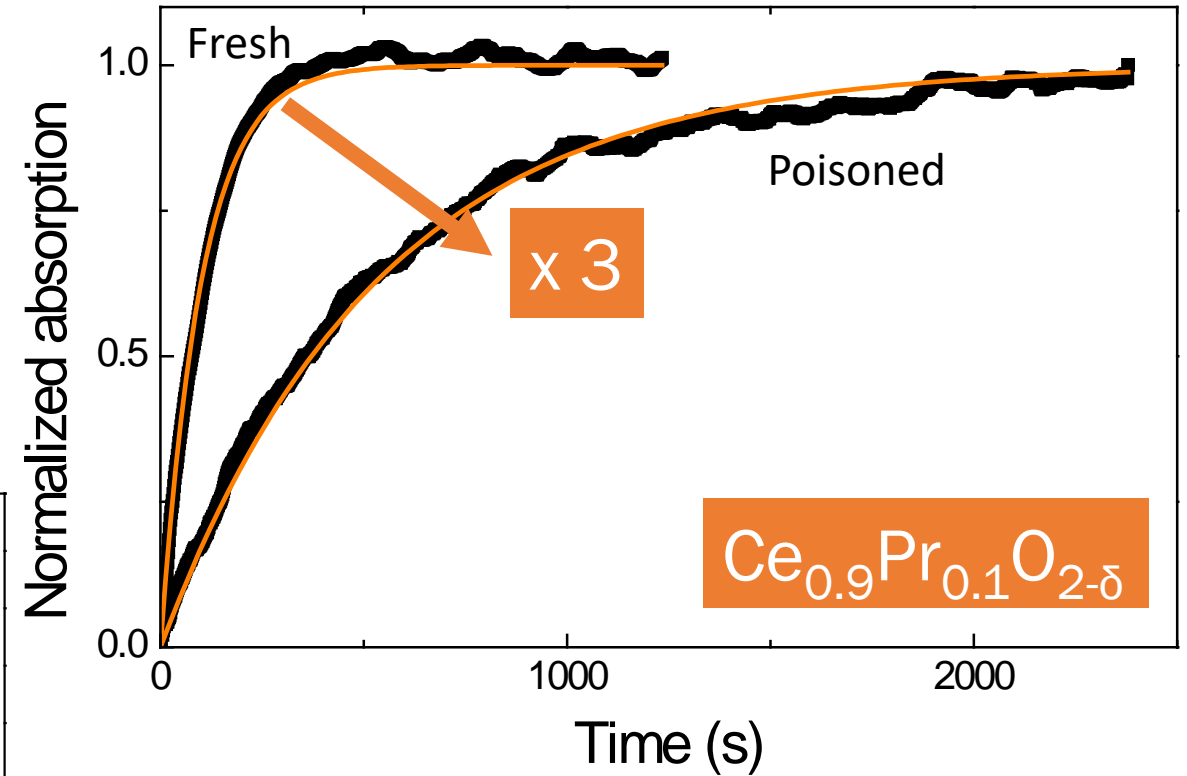
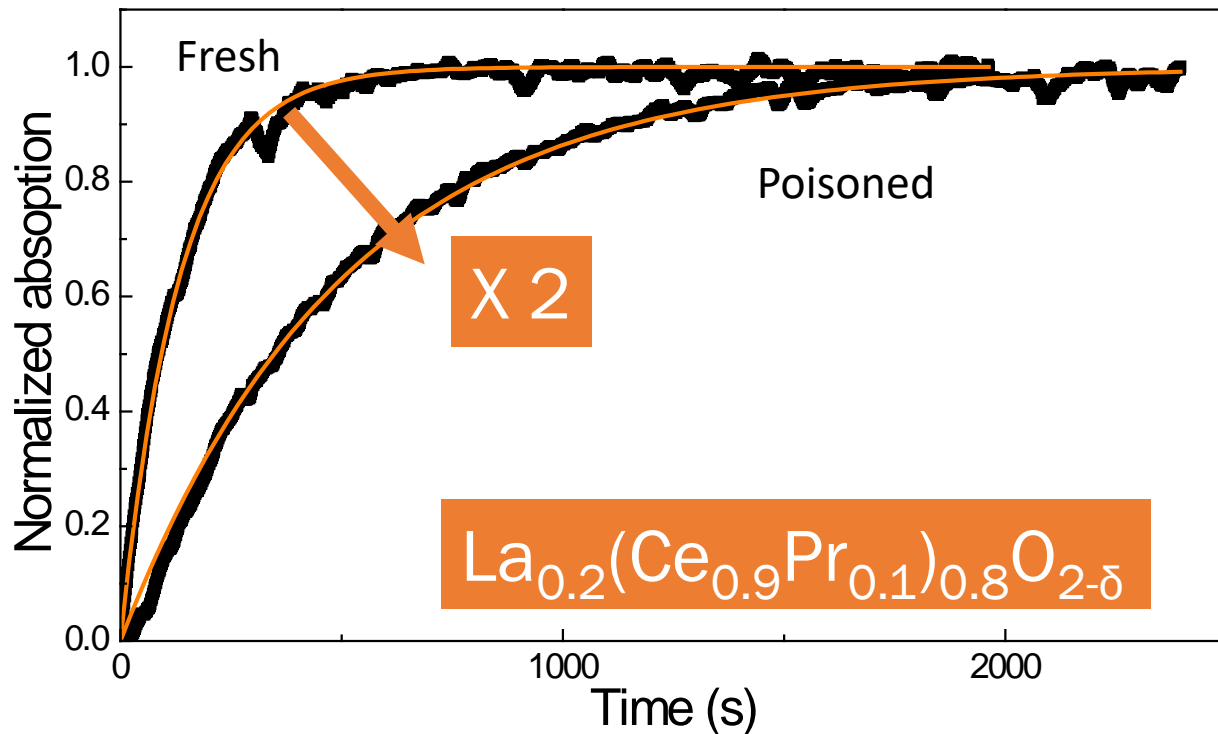
Resistance to Si poisoning

Poisoning with TEOS (10 ppm)



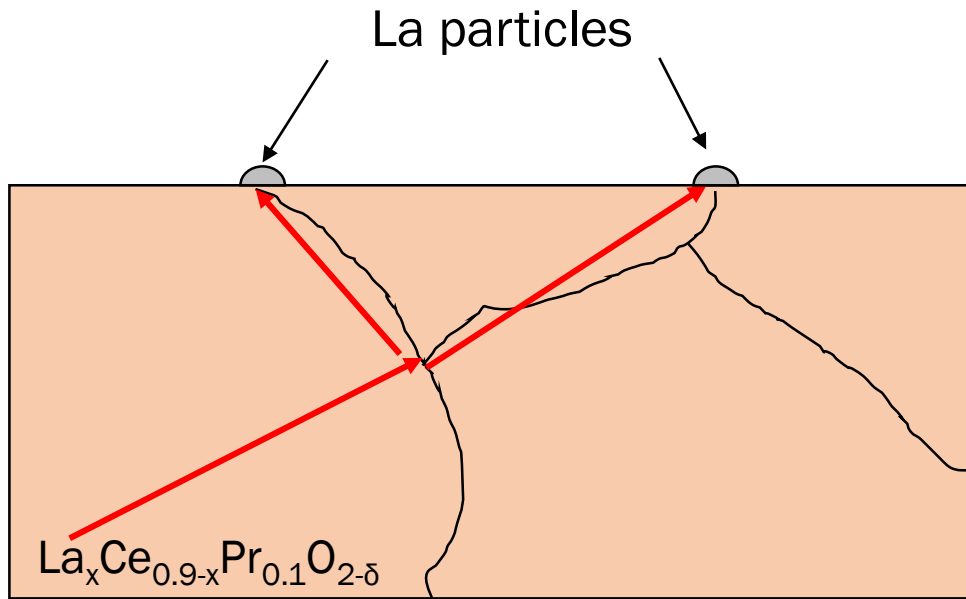
Pr/La doped Ceria film (PLD)

Y doped zirconia substrate



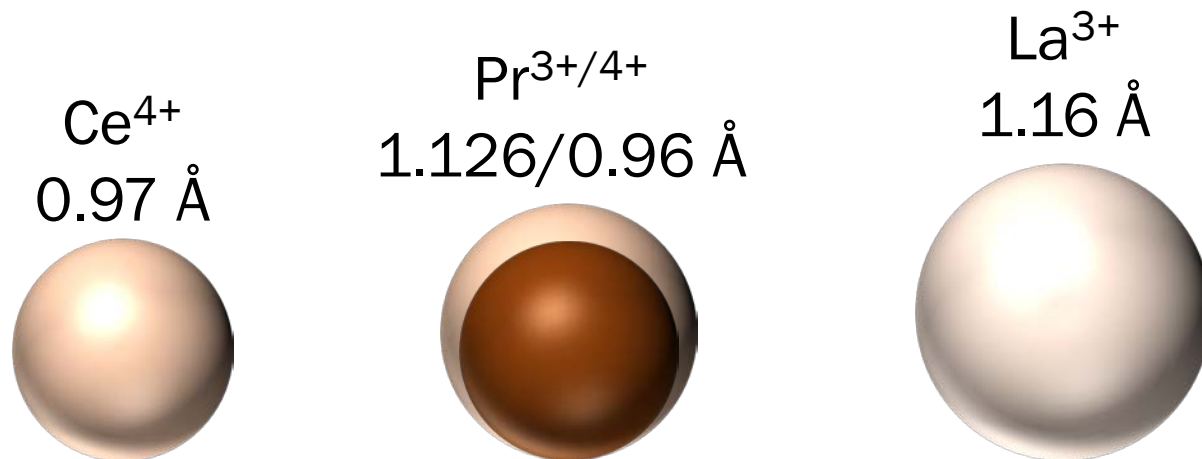
La doping → Slightly lower degradation
More La on surface?

How to induce lanthanum segregation



Driving forces for segregation:

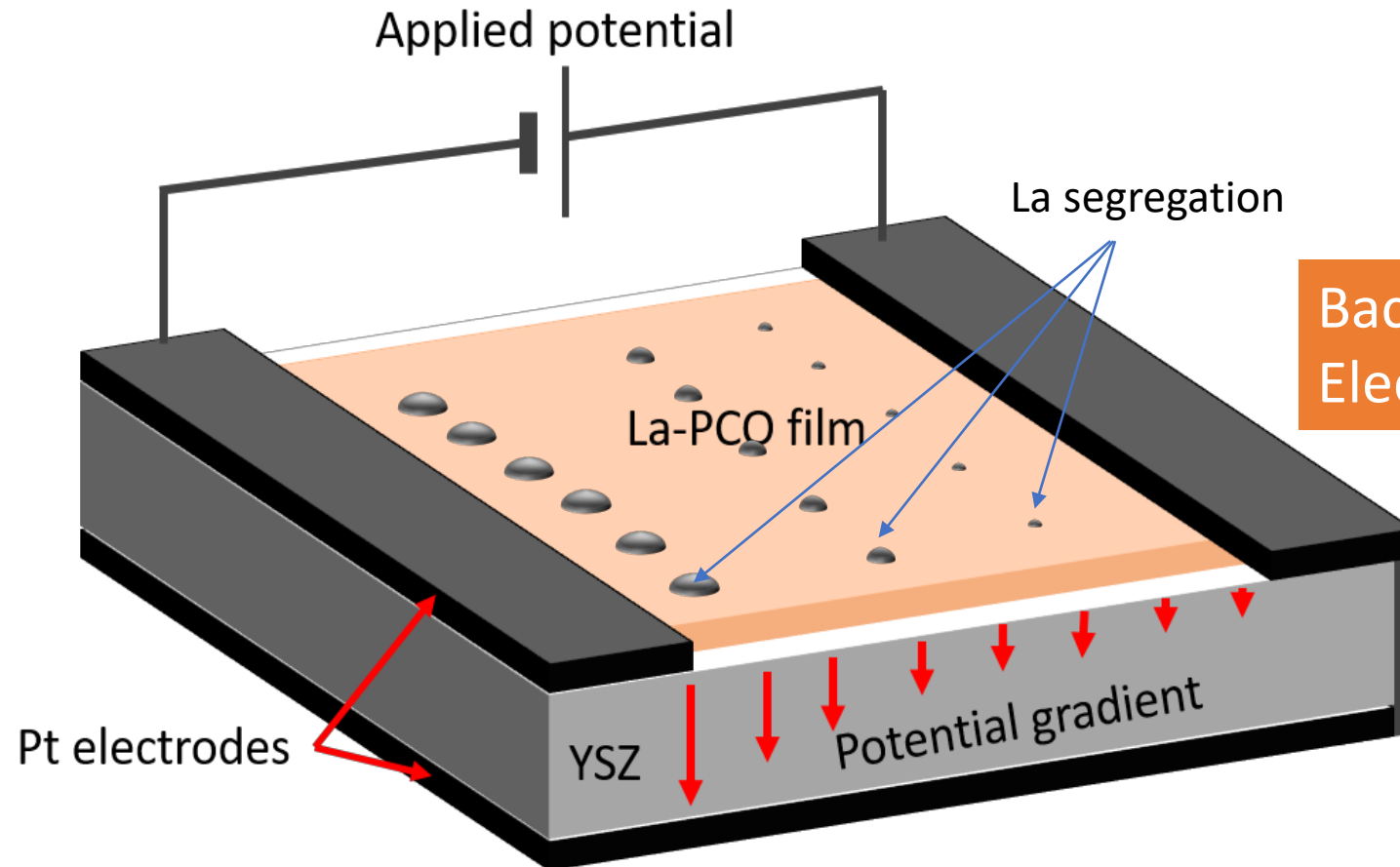
- Lattice strain
- Electrostatic potential gradient



Reduction/Oxidation?
Electrical potential effect?

How to induce lanthanum segregation

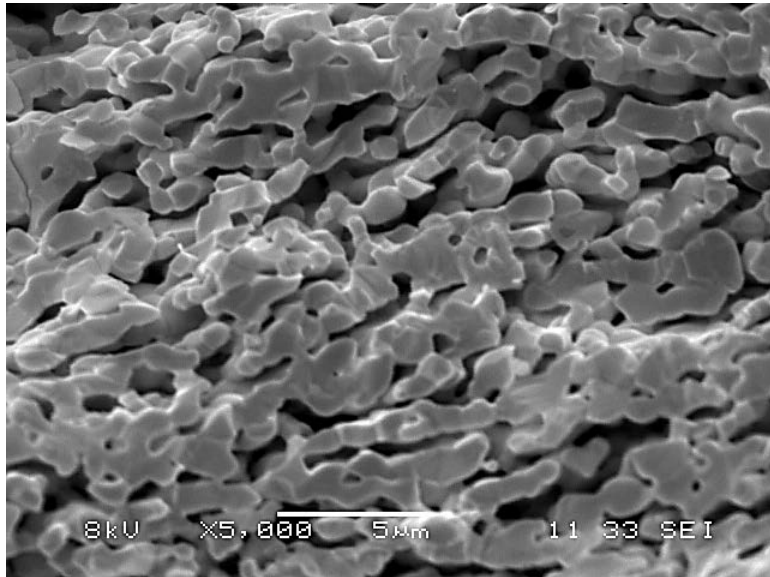
Electrical potential \rightarrow reduction of Pr \rightarrow change in lattice strain
 \rightarrow migration of charged defects (La'_{Ce})



Back-electrode setup: systematic study
Electrical potential / La segregation

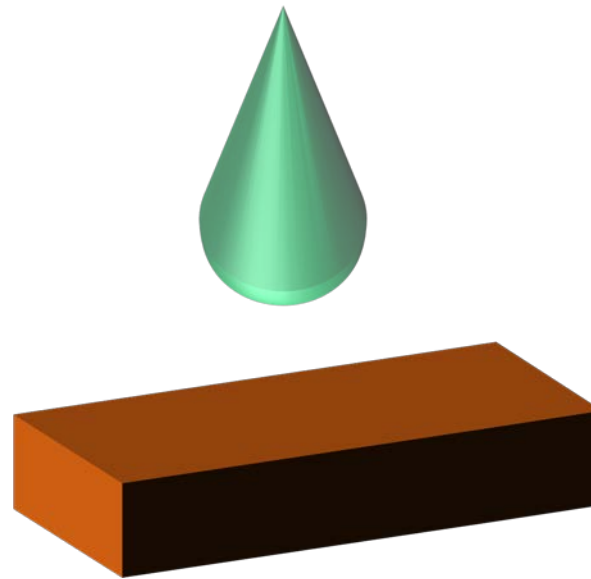
Influence of surface La on k_{chem}

Preparation of Porous PCO bars



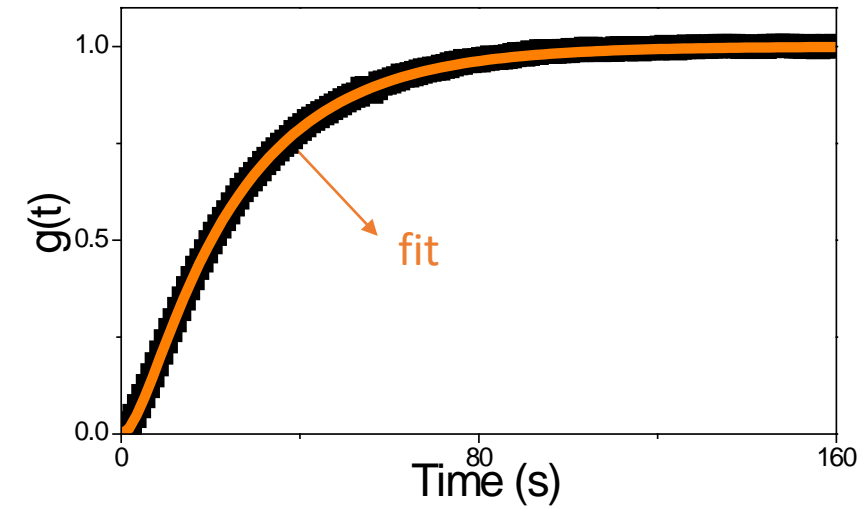
Pressing + sintering

Infiltration with La nitrate



Calcination 600°C

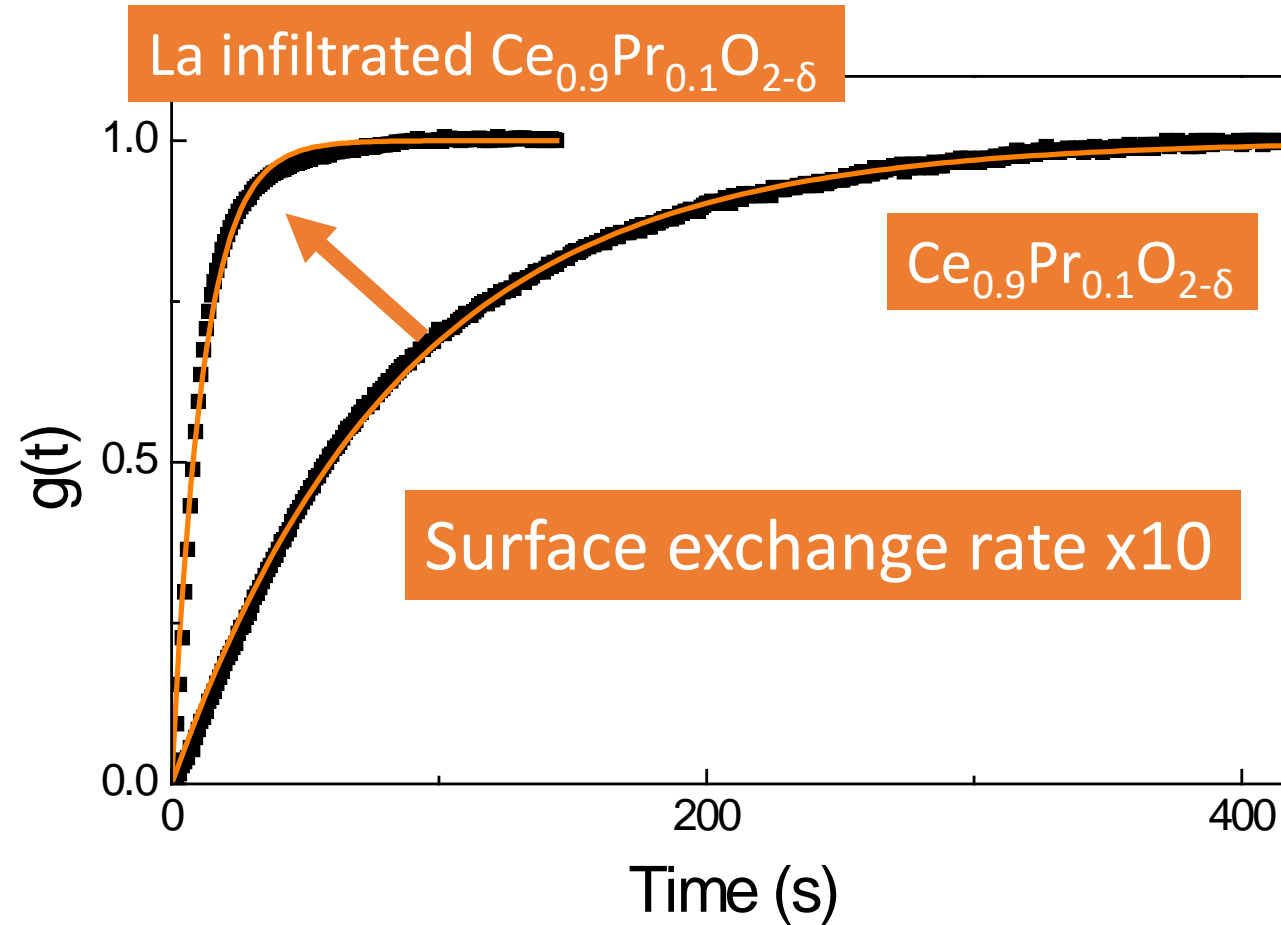
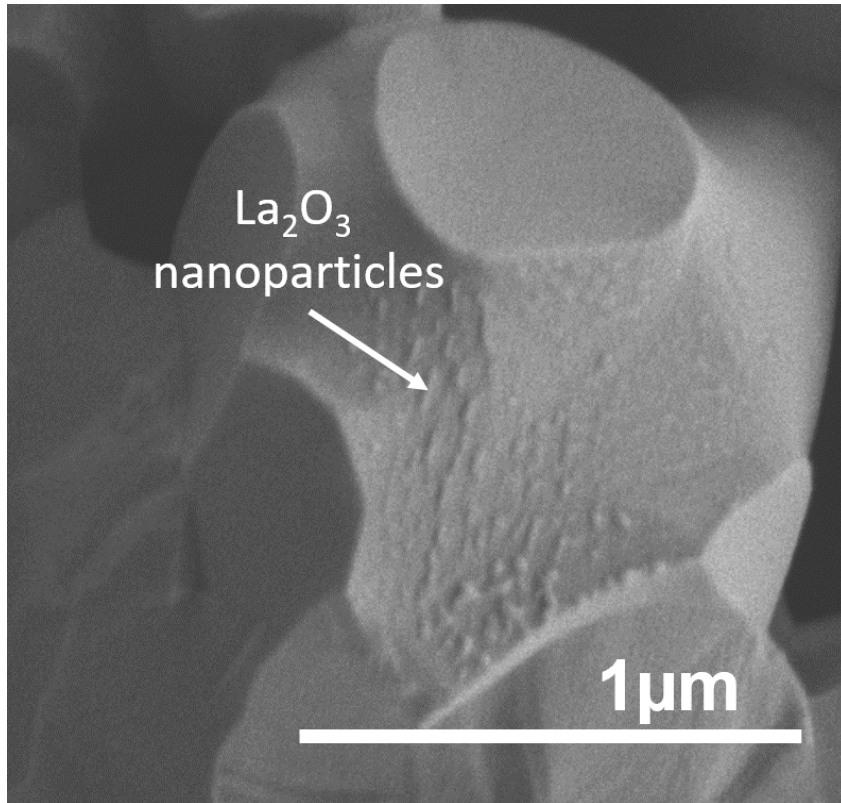
Conductivity relaxation
Surface exchange rate



$G(t)$: normalized conductivity

Surface modification: La infiltration

Comparison of surface exchange rates w/ & w/o La infiltration



Oxygen exchange rate increased with single valent oxide?

Conclusions

Best conductivity for intermediate composition $\text{La}_{0.1}(\text{Pr}_{0.1}\text{Ce}_{0.9})_{0.9}\text{O}_{2-\delta}$

Increase of surface exchange rates with $\text{La}_{0.2}(\text{Pr}_{0.1}\text{Ce}_{0.9})_{0.8}\text{O}_{2-\delta}$

Slight improvement of Si poisoning resistance with La doping

Surface exchange x10 with La infiltration

Perspectives

Long term continuous poisoning experiments

Segregation of La through reducing treatment or electrical potential

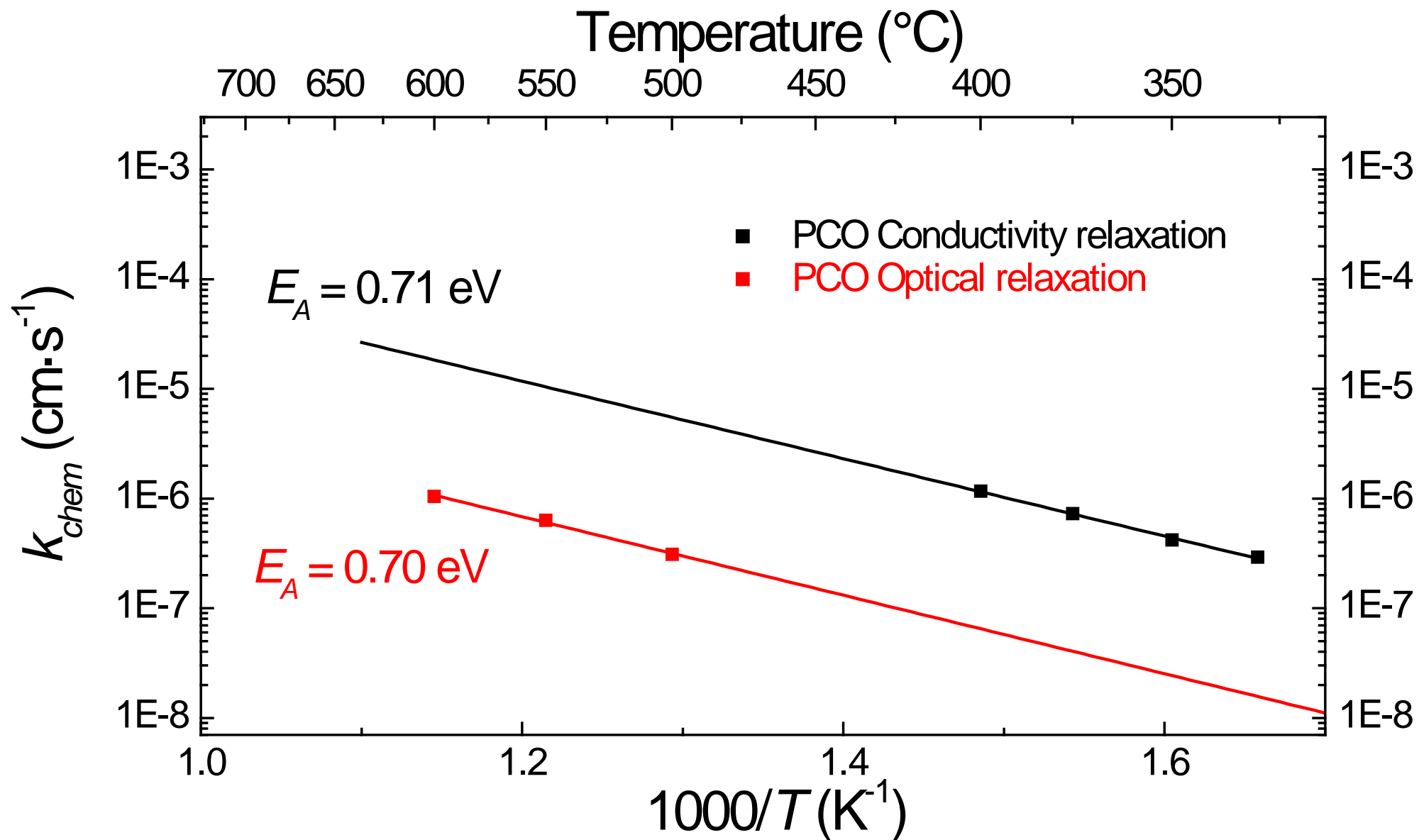
Surface analysis to better understand La influence on surface exchange

Other elements?

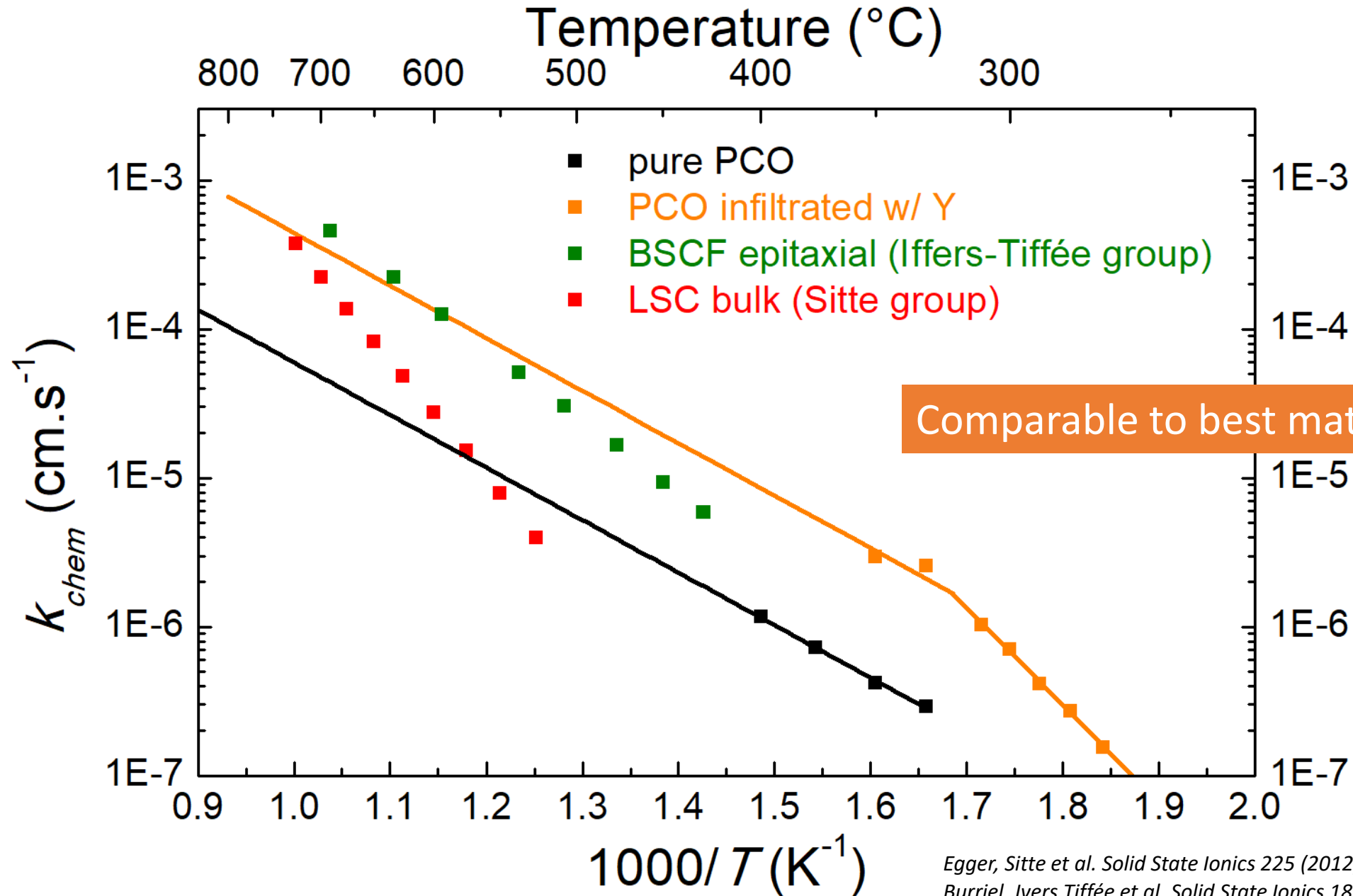
Acknowledgment: NETL Award DE-FE0026109 Phase 1
Program Manager: Dr. Joseph Stoffa

Thank you for your attention

Comparison PCO bulk and film k_{chem}



Surface modification: Oxygen surface exchange rate



Comparable to best materials in literature

Egger, Sitte et al. *Solid State Ionics* 225 (2012) 55–60
Burriel, Ivers Tiffée et al. *Solid State Ionics* 181 (2010) 602–608